

THIS SHEET HAS BEEN
REPLACED

ABSTRACT OF THE DISCLOSURE

In a magnetoresistance effect element, a pinning layer (antiferromagnetic layer) has a composition of Ru-Mn or Ru-M-Mn where M represents at least one selected from Rh, Pt, Pd, Au, Ag and Re, and impurity concentrations of the pinning layer are regulated. Accordingly, there can be provided the magnetoresistance effect element having a magnetic multilayered film which is excellent in corrosion resistance, thermal stability and magnetic field sensitivity and has a large MR change ratio, as well as a magnetoresistance device, such as a magnetoresistance effect type head or the like, using such a magnetoresistance effect element.

Figure : None

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